

BABA et al
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AMENDMENTS TO THE TITLE:

Please amend the title as follows:

SEMICONDUCTOR DEVICE WITH NMOS INCLUDING Si:C CHANNEL
REGION AND/OR PMOS INCLUDING SiGe CHANNEL REGION

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 12, line 15, as follows:

In the same apparatus, the epitaxial growth gas is replaced with a SiH₄ gas to epitaxially grow a Si film 6 having a thickness of 5 nm to 20 nm. Here, the maximum thickness of the Si film 6 is fixed because the channel of the nMOS is produced in the C-containing Si film 5, but the thickness thereof may be adjusted as appropriate in consideration of the thickness of the gate insulator ~~electrode~~ 8, the dopant concentration in the Si film 6, the offset value of zone energy between the C-containing Si film 5 and the Si film 6. For example, if the gate insulator ~~electrode~~ 8 is 2.5 nm thick, the carbon concentration is 0.5 % and the dopant concentration is $3 \times 10^{17} \text{ cm}^{-3}$, the Si film 6 may preferably be about 2 nm to 6.5 nm thick in consideration of reduction in the thickness of the film at gate oxidation.